

# Burcu Arpapay

## List of Publications by Year in descending order

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9  
papers

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citations

2258059

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2053705

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10  
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10  
docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	The investigation of photoluminescence properties in $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ multiple quantum wells structures with varying well number. <i>Physica B: Condensed Matter</i> , 2022, 630, 413703.	2.7	4
2	A comparative study on GaSb epilayers grown on nominal and vicinal Si(100) substrates by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2021, 36, 025011.	2.0	6
3	Convex-like GaAs nanowires grown on Si (111) substrates. <i>Materials Science in Semiconductor Processing</i> , 2020, 107, 104817.	4.0	1
4	Influence of growth parameters on the morphology of GaAs nanowires grown on Si (111) by molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2020, 111, 104990.	4.0	2
5	The role of antiphase domain boundary density on the surface roughness of GaSb epilayers grown on Si (001) substrates. <i>Superlattices and Microstructures</i> , 2020, 140, 106450.	3.1	4
6	Structural and optical characterization of GaSb on Si (001) grown by Molecular Beam Epitaxy. <i>Semiconductor Science and Technology</i> , 2019, 34, 035013.	2.0	8
7	A comparative photoluminescence study on Mn-Free GaAs/AlAs and Mn-containing $\text{Ga}_{1-x}\text{Mn}_x\text{As}/\text{AlAs}$ quantum wells (QWs) grown on various orientations by MBE. <i>Philosophical Magazine</i> , 2016, 96, 223-229.	1.6	2
8	Redundant Sb condensation on GaSb epilayers grown by molecular beam epitaxy during cooling procedure. <i>Thin Solid Films</i> , 2014, 564, 110-114.	1.8	2
9	Structural and Optical Properties of Electrochemically Grown Fluorine Doped Zinc Oxide Rods. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2014, 9, 590-595.	0.5	1